1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a CFP15 (SOT1289) power and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: I_{F(AV)} ≤ 15 A
- Reverse voltage: V_R ≤ 45 V
- Extremely low forward voltage
- · High power capability due to clip-bonding technology and heat sink
- Small and thin SMD power plastic package, typical height 0.78 mm
- AEC-Q101 qualified

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Freewheeling application
- Reverse polarity protection
- Low power consumption application

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; T _{sp} ≤ 160 °C; square wave	-	-	15	A
V_R	reverse voltage	T _j = 25 °C	-	-	45	V
V _F	forward voltage	I_F = 15 A; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C; pulsed	-	430	490	mV
I _R	reverse current	V_R = 10 V; $t_p \le 3$ ms; $\overline{o} \le 0.3$; T_j = 25 °C; pulsed	-	30	70	μA
		V_R = 45 V; $t_p \le 3$ ms; $δ \le 0.3$; T_j = 25 °C; pulsed	-	420	900	μA





5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Α	anode		K PA
2	Α	anode	3	aaa-009063
3	K	cathode	2 CFP15 (SOT1289)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMEG045V150EPD	CFP15	plastic, thermal enhanced ultra thin SMD package; 3 leads; body: 5.8 x 4.3 x 0.78 mm	SOT1289			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG045V150EPD	045V 150E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	T _j = 25 °C		-	45	V
I _F	forward current	T _{sp} = 155 °C; δ = 1		-	21	Α
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; $T_{sp} \le$ 160 °C; square wave		-	15	A
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	270	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.66	W
			[2]	-	2.15	W
			[3]	-	3.75	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

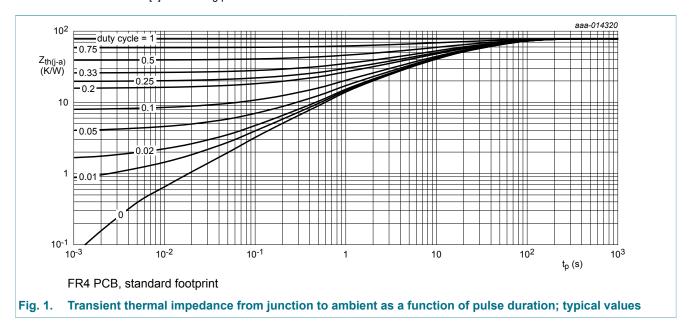
^[3] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

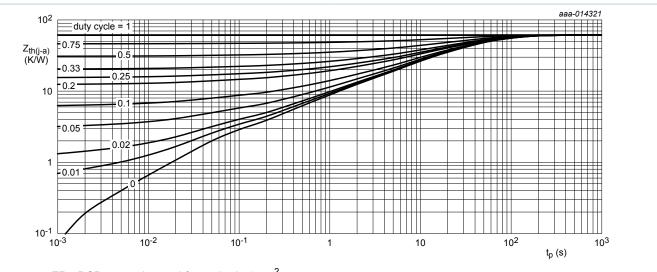
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fron	thermal resistance	in free air	[1][2]	-	-	90	K/W
	from junction to ambient		[1][3]	-	-	70	K/W
	ambient		[1][4]	-	-	40	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	3	K/W

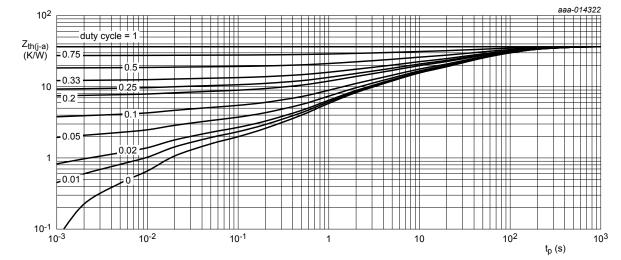
- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.





FR4 PCB, mounting pad for cathode 1 cm²

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



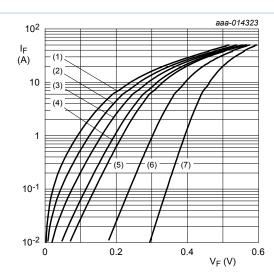
Ceramic PCB, Al₂O₃, standard footprint

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)R}$	reverse breakdown voltage	I_R = 5 mA; T_j = 25 °C; t_p ≤ 1.2 ms; δ ≤ 0.12; pulsed	45	-	-	V
V _F	forward voltage	I_F = 1 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed	-	305	350	mV
		I_F = 5 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed	-	360	410	mV
		I_F = 10 A; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed	-	400	-	mV
		I_F = 15 A; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C; pulsed	-	430	490	mV
		I_F = 15 A; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 125 °C; pulsed	-	335	-	mV
I _R	reverse current	V_R = 5 V; t_p ≤ 3 ms; δ ≤ 0.3; T_j = 25 °C; pulsed	-	20	-	μA
		V_R = 10 V; $t_p \le 3$ ms; $\delta \le 0.3$; T_j = 25 °C; pulsed	-	30	70	μA
		$V_R = 30 \text{ V}; t_p \le 3 \text{ ms}; \ \overline{o} \le 0.3;$ $T_j = 25 \text{ °C}; \text{ pulsed}$	-	90	-	μA
		$V_R = 45 \text{ V}; t_p \le 3 \text{ ms}; \delta \le 0.3;$ $T_j = 25 \text{ °C}; \text{ pulsed}$	-	420	900	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	1870	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	610	-	pF
t _{rr}	reverse recovery time step recovery	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 ^{\circ}\text{C}$	-	54	-	ns
t _{rr}	reverse recovery time ramp recovery	$dI_F/dt = 200 \text{ A/}\mu\text{s}; T_j = 25 \text{ °C}; I_F = 6 \text{ A};$ $V_R = 26 \text{ V}$	-	19	-	ns
V_{FRM}	peak forward recovery voltage	$I_F = 0.5 \text{ A}; dI_F/dt = 20 \text{ A/}\mu\text{s}; T_j = 25 ^{\circ}\text{C}$	-	294	-	mV



pulsed condition

(1) $T_i = 175 \, ^{\circ}C$

(2) $T_i = 150 \, ^{\circ}C$

(3) $T_i = 125 \, ^{\circ}C$

(4) $T_j = 100 \, ^{\circ}C$

 $(5) T_i = 85 °C$

(6) $T_j = 25 \,^{\circ}C$

 $(7) T_i = -40 °C$

Fig. 4. Forward current as a function of forward voltage; typical values

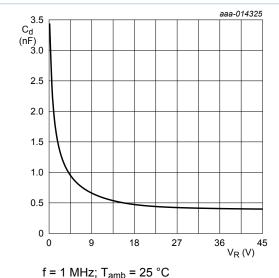
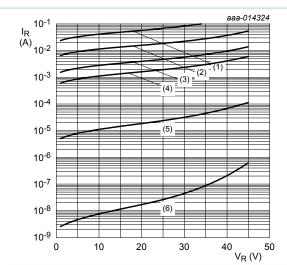


Fig. 6. Diode capacitance as a function of reverse voltage; typical values



pulsed condition

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_i = 125 \, ^{\circ}C$

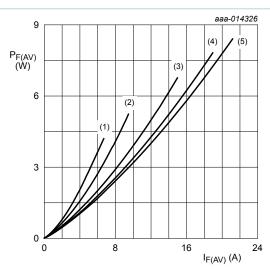
(3) $T_i = 100 \,^{\circ}\text{C}$

(4) $T_i = 85 \,^{\circ}C$

 $(5) T_{i} = 25 ^{\circ}C$

(6) $T_i = -40 \, ^{\circ}C$

Fig. 5. Reverse current as a function of reverse voltage; typical values



T_i = 100 °C

 $(1) \delta = 0.1$

 $(2) \delta = 0.2$

 $(3) \delta = 0.5$

 $(4) \delta = 0.8$

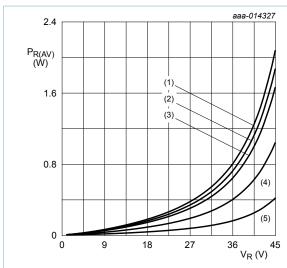
 $(5) \delta = 1$

Fig. 7. Average forward power dissipation as a function of average forward current; typical values

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 $T_i = 100 \, ^{\circ}C$

 $(1) \delta = 1$

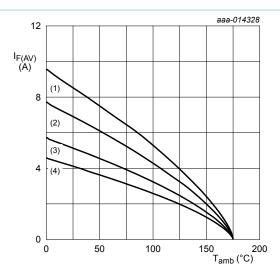
 $(2) \delta = 0.9$

 $(3) \delta = 0.8$

 $(4) \delta = 0.5$

 $(5) \delta = 0.2$

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T_j = 175 °C

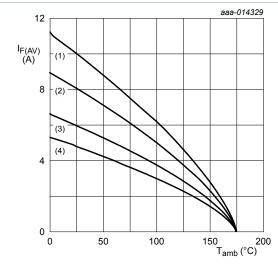
(1) δ = 1; DC

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

 T_i = 175 °C

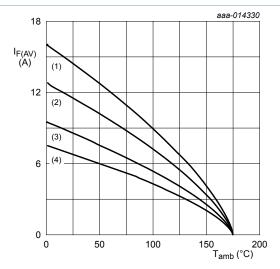
(1) δ = 1; DC

(2) $\delta = 0.5$; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

 $T_i = 175 \,{}^{\circ}\text{C}$

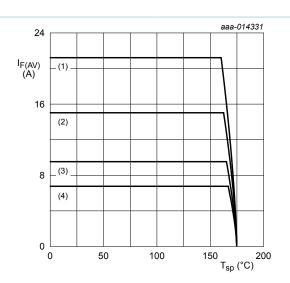
(1) δ = 1; DC

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



T_i = 175 °C

(1) δ = 1; DC

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 12. Average forward current as a function of solder point temperature; typical values

11. Test information

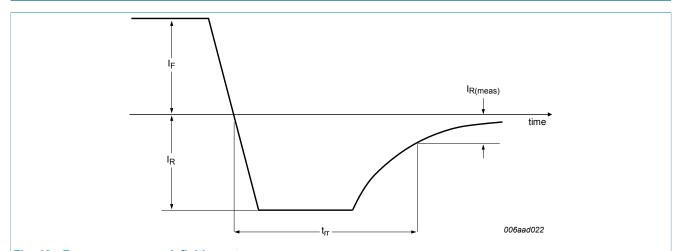


Fig. 13. Reverse recovery definition; step recovery

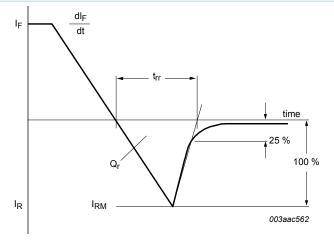


Fig. 14. Reverse recovery definition; ramp recovery

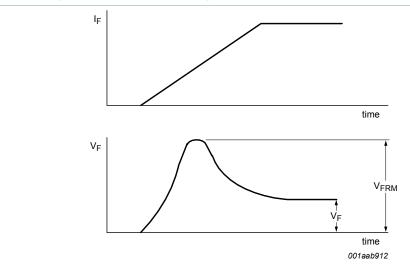


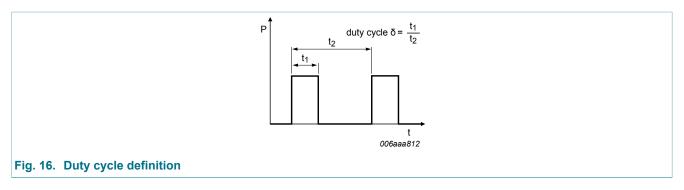
Fig. 15. Forward recovery definition

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Product data sheet

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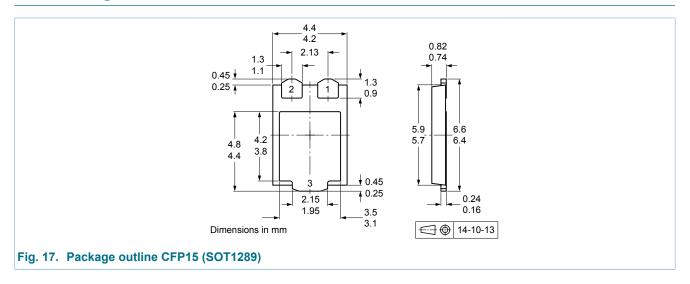


The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

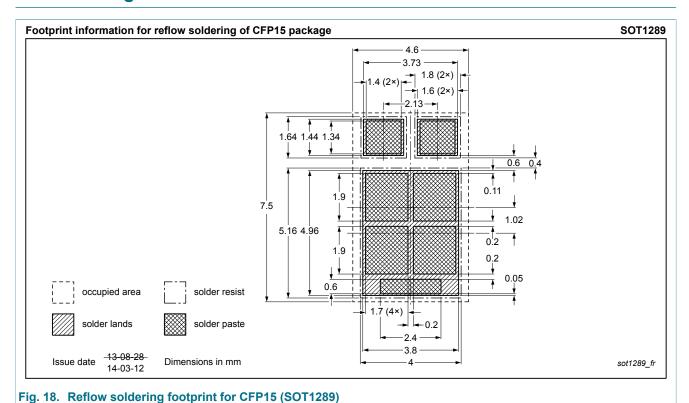
11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG045V150EPD v.4	20150122	Product data sheet	-	PMEG045V150EPD v.3
Modifications:	Table characteristic	s: corrected t _{rr} value		
PMEG045V150EPD v.3	20150121	Product data sheet	-	PMEG045V150EPD v.2
PMEG045V150EPD v.2	20140704	Preliminary data sheet	-	PMEG045V150EPD v.1
PMEG045V150EPD v.1	20140519	Objective data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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